

NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

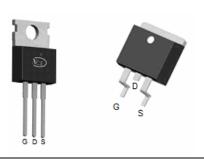
• V_{DS} =100V,I_D =125A

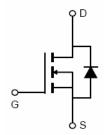
 $R_{DS(ON)}\!\!=\!\!4.2m\Omega \text{ , typical (TO-220)@ }V_{GS}\!\!=\!\!10V$ $R_{DS(ON)}\!\!=\!\!4.0m\Omega \text{ , typical (TO-263)@ }V_{GS}\!\!=\!\!10V$

- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175°C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

TO-220 TO-263





Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP045N10	NCEP045N10	TO-220-3L	-	-	-
NCEP045N10D	NCEP045N10D	TO-263	-	-	-

Absolute Maximum Ratings (T_c=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	100	V
Gate-Source Voltage	V _G S	±20	V
Drain Current-Continuous	I _D	125	Α
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	95	Α
Pulsed Drain Current	I _{DM}	500	Α
Maximum Power Dissipation	P _D	200	W
Derating factor		1.33	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	871	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}\!\mathbb{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2) ReJC 0.75 °C/W
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Electrical Characteristics (T_C=25°C unless otherwise noted)

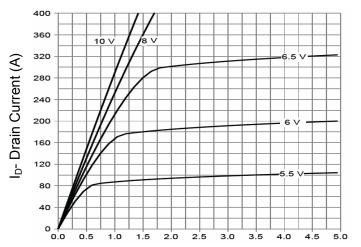
Parameter	Symbol	Condition		Min	Тур	Max	Unit
Off Characteristics				•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA		100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V		-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V		-	-	±100	nA
On Characteristics (Note 3)				•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=$	250µA	2	3	4	V
Drain-Source On-State Resistance	В	V _{GS} =10V, I _D =60A	TO-220	-	4.2	4.5	0
Diain-Source On-State Resistance	rain-Source On-State Resistance $R_{DS(ON)}$ V_{GS} =10V, I_D =60A TO -26	TO-263		4.0	4.5	mΩ	
Forward Transconductance	g FS	V _{DS} =5V,I _D =	=60A		120	-	S
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}	- V _{DS} =50V,V _{GS} =0V, F=1.0MHz		-	5500	-	PF
Output Capacitance	Coss			-	590	-	PF
Reverse Transfer Capacitance	C _{rss}			-	25	-	PF
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}	V_{DD} =50V, I_{D} =60A, V_{GS} =10V, R_{G} =3 Ω		-	21	-	nS
Turn-on Rise Time	t _r			-	13	-	nS
Turn-Off Delay Time	t _{d(off)}			-	40	-	nS
Turn-Off Fall Time	t _f			-	12	-	nS
Total Gate Charge	Qg	- V _{DS} =50V,I _D =60A, - V _{GS} =10V		-	92	-	nC
Gate-Source Charge	Q _{gs}			-	27		nC
Gate-Drain Charge	Q_{gd}			-	21		nC
Drain-Source Diode Characteristics	•					•	
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =60A		-		1.2	V
Diode Forward Current (Note 2)	Is			-	-	125	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =60A		-	72	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$		-	140	-	nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V $_{\text{DD}}$ =50 V,V $_{\text{G}}$ =10 V,L=0.5 mH,Rg=25 Ω

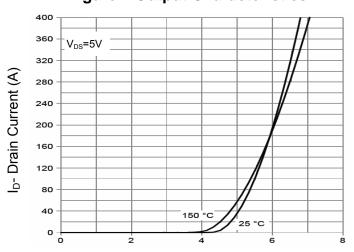


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

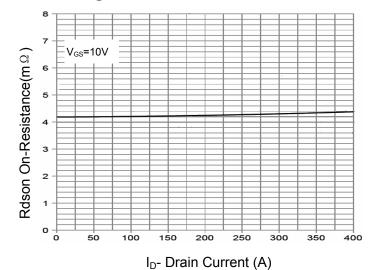
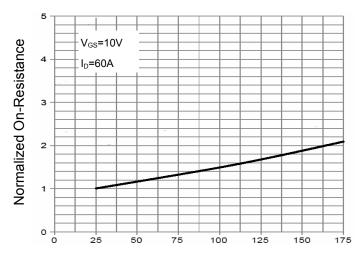
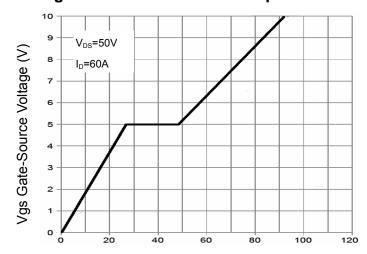


Figure 3 Rdson- Drain Current

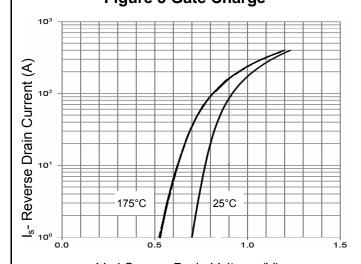


T_J-Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature



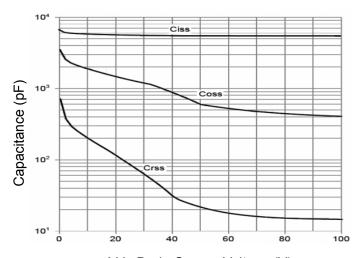
Qg Gate Charge (nC)
Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward



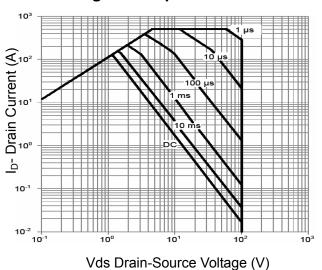


250 Power Dissipation (W) 50 200

Vds Drain-Source Voltage (V)

Figure 7 Capacitance vs Vds

 T_J -Junction Temperature($^{\circ}$ C) Figure 9 Power De-rating



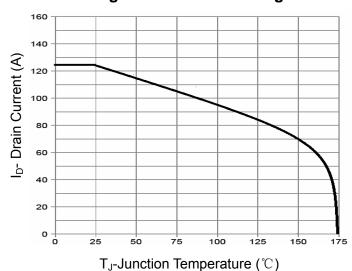


Figure 8 Safe Operation Area

Figure 10 Current De-rating

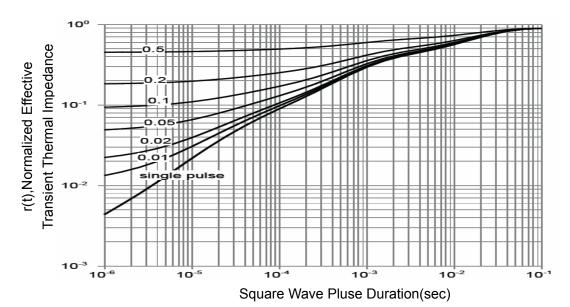
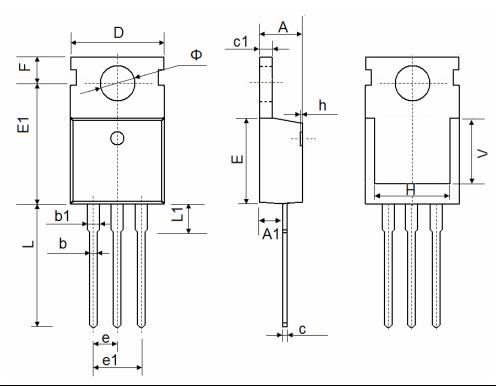


Figure 11 Normalized Maximum Transient Thermal Impedance

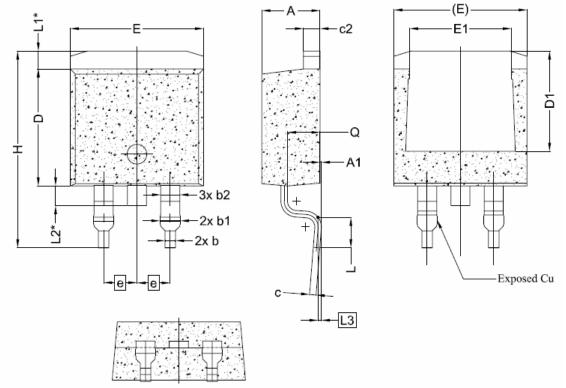
TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.90	0 REF.	0.276 REF.		
Ф	3.400	3.800	0.134	0.150	



TO-263-2L Package Information



Cumbal	Dimensions In Millimeters				
Symbol	Min.	Nom.	Max.		
А	4.24	4.44	4.64		
A1	0.00	0.10	0.25		
b	0.70	0.80	0.90		
b1	1.20	1.55	1.75		
b2	1.20	1.45	1.70		
С	0.40	0.50	0.60		
c2	1.15	1.15 1.27			
D	8.82	8.92	9.02		
D1	6.86	7.65	-		
E	9.96	10.16	10.36		
E1	6.89	7.77	7.89		
е	2.54BSC				
Н	14.61	14.61 15.00			
L	1.78	1.78 2.32			
L1	1.36 REF.				
L2	1.50 REF.				
L3	0.25 BSC				
Q	2.30	2.48 2.70			



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